

# PolarHV™ HiPerFET Power MOSFET

**IXFK 32N80P**  
**IXFX 32N80P**

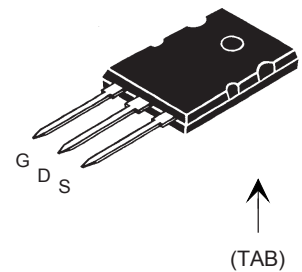
$V_{DSS} = 800 \text{ V}$   
 $I_{D25} = 32 \text{ A}$   
 $R_{DS(on)} \leq 270 \text{ m}\Omega$   
 $t_{rr} \leq 250 \text{ ns}$

N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode

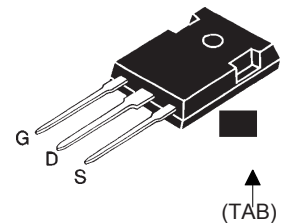


Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	800	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1 \text{ M}\Omega$	800	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	32	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	70	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	16	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	50	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	2.0	J
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 4 \Omega$	10	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	830	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
$T_{SOLD}$	Plastic body for 10 s	260	$^\circ\text{C}$
$M_d$	Mounting torque (TO-264)	1.13/10 Nm/lb.in.	
Weight	TO-264	10	g
	PLUS247	6	g

TO-264 (IXFK)



PLUS247 (IXFX)



G = Gate    L : Drain  
S = Source    Tab = Drain

## Features

- † International standard packages
- † Fast recovery diode
- † Unclamped Inductive Switching (UIS) rated
- † Low package inductance - easy to drive and to protect

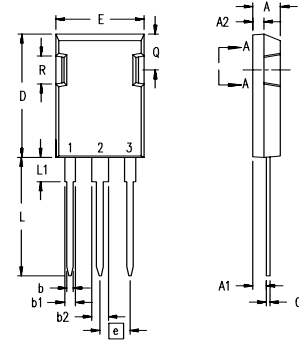
## Advantages

- † Easy to mount
- † Space savings
- † High power density

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	800		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8 \text{ mA}$	3.0		5.0 V
$I_{GSS}$	$V_{GS} = \pm 30 \text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 200 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			25 $\mu\text{A}$
				1000 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$ , duty cycle $d \leq 2 \%$			270 $\text{m}\Omega$

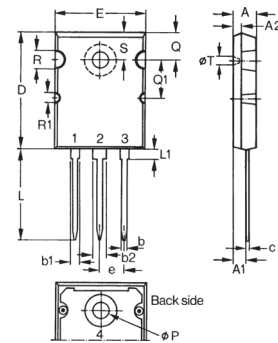
Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ unless otherwise specified)		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20\text{ V}; I_D = 0.5 I_{D25}$ , pulse test	23	38	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		8800	pF
$C_{oss}$			700	pF
$C_{rss}$			26	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2\ \Omega$ (External)		30	ns
$t_r$			24	ns
$t_{d(off)}$			85	ns
$t_f$			24	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		150	nC
$Q_{gs}$			40	nC
$Q_{gd}$			44	nC
$R_{thJC}$			0.15	$^\circ\text{C/W}$
$R_{thCS}$		0.15		$^\circ\text{C/W}$

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ unless otherwise specified)		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{ V}$			32 A
$I_{SM}$	Repetitive			70 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}, V_{GS} = 0\text{ V}$			250 ns
$Q_{RM}$			0.8	$\mu\text{C}$
$I_{RM}$			6.0	A

**PLUS 247™ Outline**


Terminals: 1 - Gate  
2 - Drain (Collector)  
3 - Source (Emitter)  
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A <sub>1</sub>	2.29	2.54	.090	.100
A <sub>2</sub>	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b <sub>1</sub>	1.91	2.13	.075	.084
b <sub>2</sub>	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

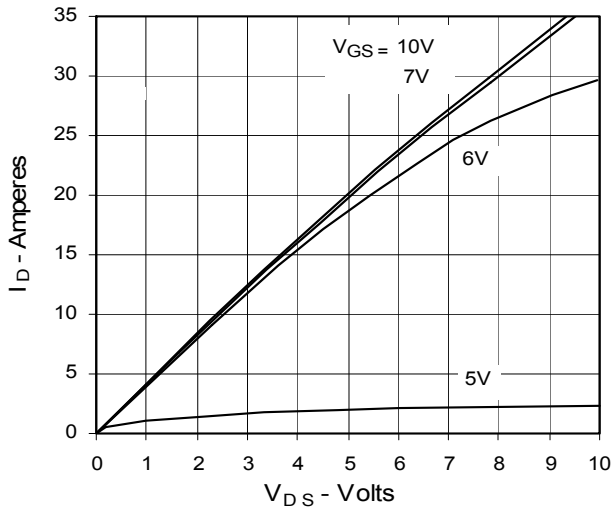
**TO-264 Outline**


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A <sub>1</sub>	2.54	2.89	.100	.114
A <sub>2</sub>	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b <sub>1</sub>	2.39	2.69	.094	.106
b <sub>2</sub>	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

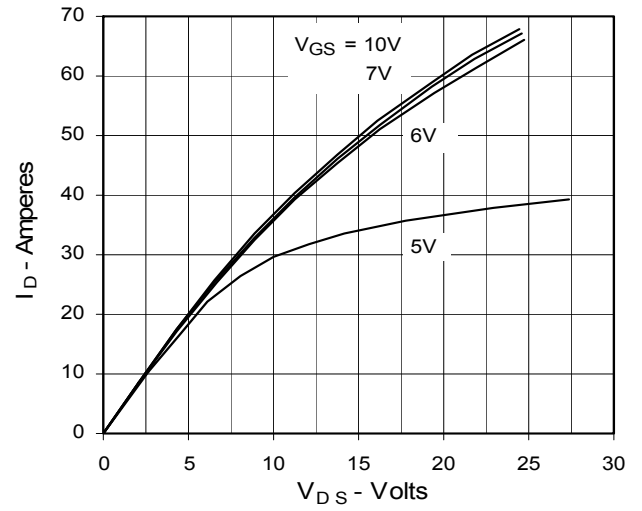
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585  
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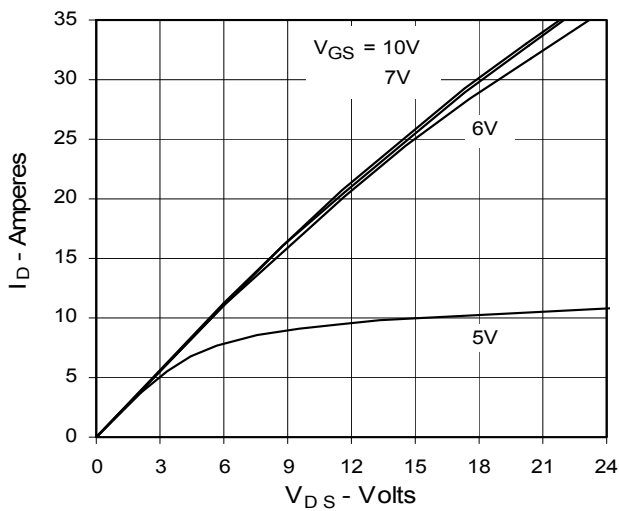
**Fig. 1. Output Characteristics**  
**@ 25°C**



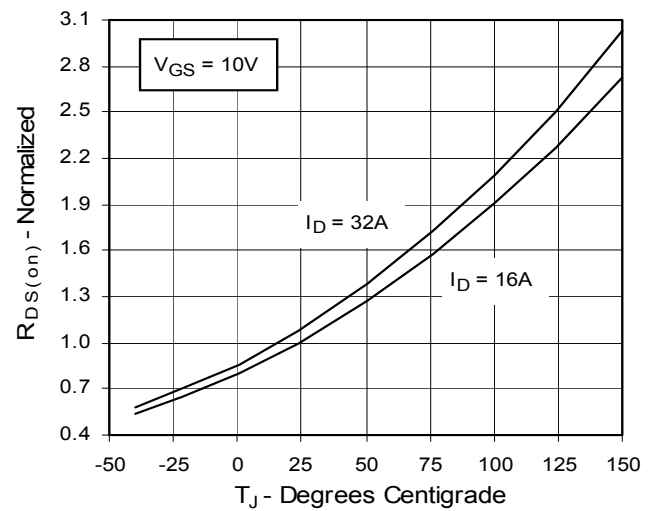
**Fig. 2. Extended Output Characteristics**  
**@ 25°C**



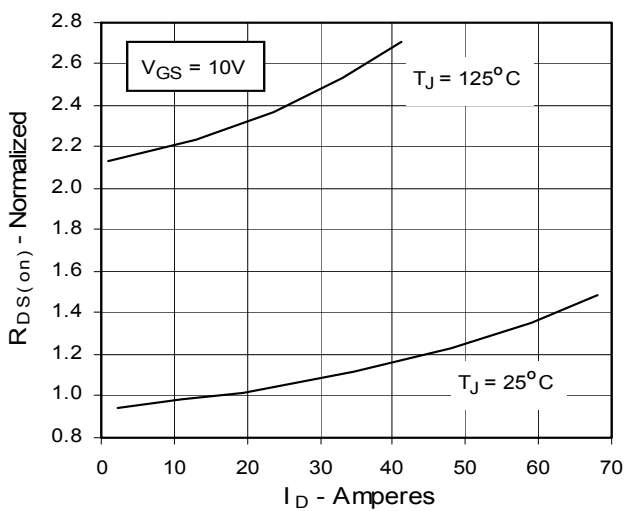
**Fig. 3. Output Characteristics**  
**@ 125°C**



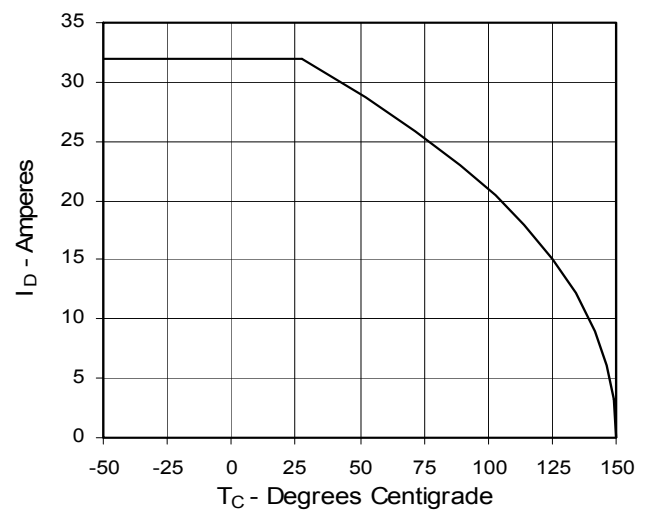
**Fig. 4.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs. Junction Temperature**



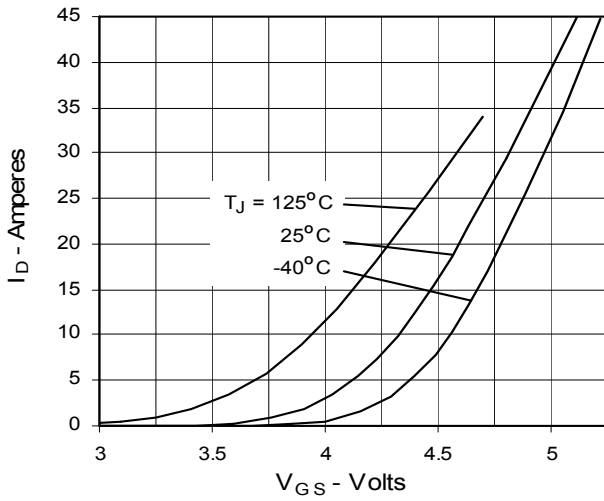
**Fig. 5.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs.  $I_D$**



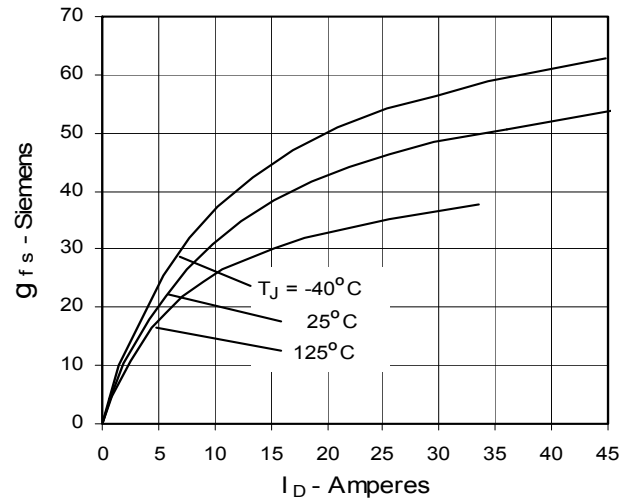
**Fig. 6. Drain Current vs. Case Temperature**



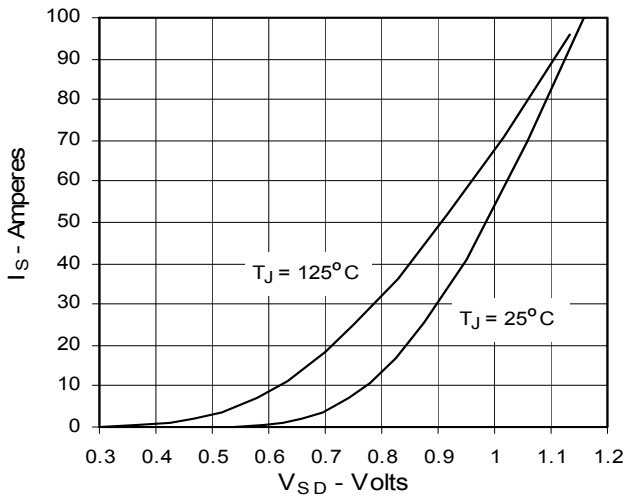
**Fig. 7. Input Admittance**



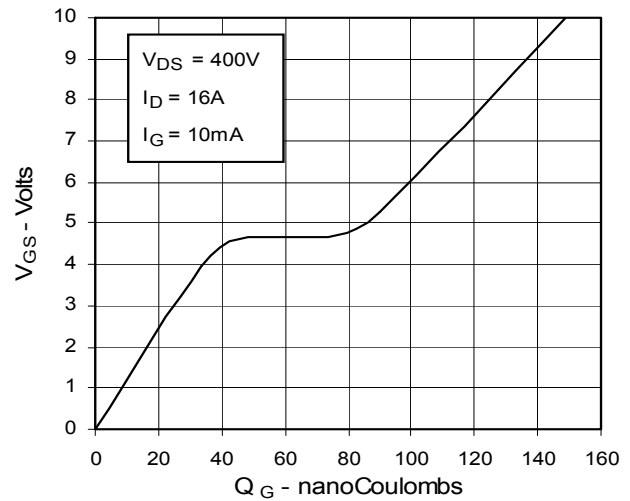
**Fig. 8. Transconductance**



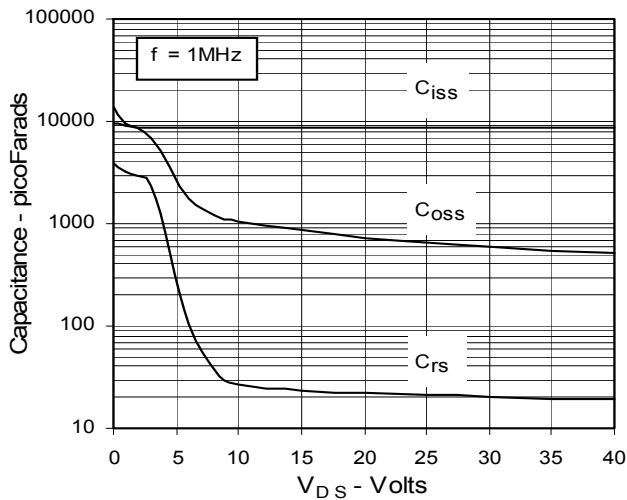
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



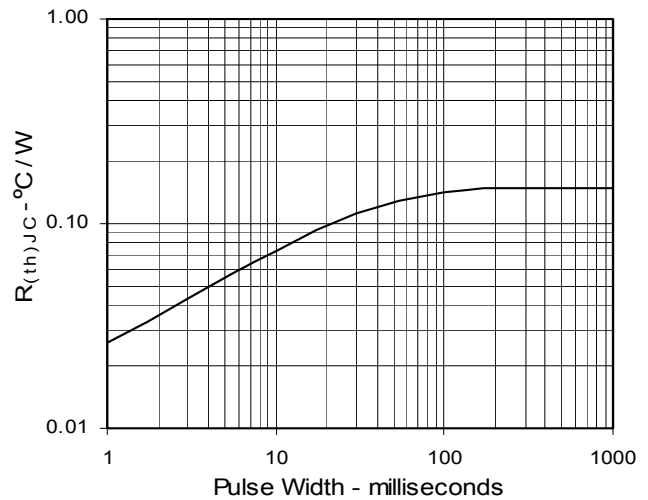
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Resistance**





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